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3	US20110181749	SOLID-STATE IMAGING DEVICE AND MANUFACTURING METHOD THEREOF, DRIVING METHOD OF SOLID-STATE IMAGING DEVICE, AND ELECTRONIC EQUIPMENT A solid-state imaging device includes multiple pixels formed of photoelectric converters and pixel transistors; a floating diffusion portion that exists within a region of each of the...	704
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7	US20110024857	SOLID-STATE IMAGE PICKUP ELEMENT, METHOD OF MANUFACTURING THE SAME, AND ELECTRONIC APPARATUS USING THE SAME Disclosed herein is a solid-state image pickup element, including: a semiconductor substrate; a	571

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8	US20130009224	SOLID-STATE IMAGING DEVICE, ELECTRONIC DEVICE, AND MANUFACTURING METHOD FOR SOLID-STATE IMAGING DEVICE In a manufacturing method for a solid-state imaging device, a photoelectric conversion portion including a first impurity layer whose carrier polarity is a first conductivity type is formed within...	537
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